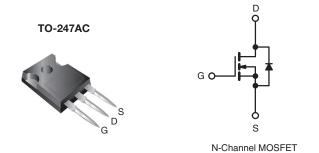


Power MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	800		
R _{DS(on)} (Ω)	V _{GS} = 10 V 1.2		
Q _g (Max.) (nC)	200		
Q _{gs} (nC)	24		
Q _{gd} (nC)	110		
Configuration	Single		



FEATURES

- · Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- · Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance cost-effectiveness.

The TO-247AC package preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION		
Package	TO-247AC	
Lead (Pb)-free	IRFPE50PbF	
Lead (FD)-life	SiHFPE50-E3	
SnPb	IRFPE50	
SIFU	SiHFPE50	

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	800	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I_	7.8	
Continuous Drain Current	VGS at 10 V	T _C = 100 °C	I _D	4.9	Α
Pulsed Drain Current ^a			I _{DM}	31	
Linear Derating Factor				1.5	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	770	mJ
Repetitive Avalanche Currenta			I _{AR}	7.8	Α
Repetitive Avalanche Energy ^a			E _{AR}	19	mJ
Maximum Power Dissipation	T _C =	25 °C	P_{D}	190	W
Peak Diode Recovery dV/dt ^c			dV/dt	2.0	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature) for 10 s		-	300 ^d	7	
Mounting Torque 6-32 or M3 screw			10	lbf ⋅ in	
Mounting Torque	0-32 OF IVIS SCIEW			1.1	N⋅m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. V_{DD} = 50 V, starting T_J = 25 °C, L = 23 mH, R_g = 25 Ω , I_{AS} = 7.8 A (see fig. 12). c. I_{SD} ≤ 7.8 A, dI/dt ≤ 140 A/ μ s, V_{DD} ≤ 600 V, T_J ≤ 150 °C.
- d. 1.6 mm from case.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R _{thJA}	-	40	
Case-to-Sink, Flat, Greased Surface	R _{thCS}	0.24	-	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.65	

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						•	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0 V, I _D = 250 μA	800	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference	e to 25 °C, I _D = 1 mA	-	0.98	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} :	= V _{GS} , I _D = 250 μA	2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}		V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}		= 800 V, V _{GS} = 0 V V, V _{GS} = 0 V, T _J = 125 °C	-	-	100 500	μА
Drain-Source On-State Resistance	R _{DS(on)}		$I_D = 4.7 \text{ A}^b$	_	_	1.2	Ω
Forward Transconductance	9fs		= 100 V, I _D = 4.7 A ^b	5.6	_		S
Dynamic	915	• 555 -	100 1, 10 - 111 71	0.0			
Input Capacitance	C _{iss}			_	3100	_	
Output Capacitance	C _{oss}	7	$V_{GS} = 0 \text{ V},$ $V_{DS} = 25 \text{ V},$	_	800	-	pF
Reverse Transfer Capacitance	C _{rss}	f = 1	.0 MHz, see fig. 5	-	490	-	
Total Gate Charge	Qg			-	-	200	
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V	$V_{GS} = 10 \text{ V}$ $I_{D} = 7.8 \text{ A}, V_{DS} = 400 \text{ V},$ see fig. 6 and 13 ^b	-	-	24	nC
Gate-Drain Charge	Q _{gd}	See lig. 0 and 10	-	-	110	1	
Turn-On Delay Time	t _{d(on)}			-	19	-	
Rise Time	t _r	V _{DD} =	$V_{DD} = 400 \text{ V}, I_{D} = 7.8 \text{ A},$		38	-	ns
Turn-Off Delay Time	t _{d(off)}	$R_g = 6.2 \Omega, R_D = 52 \Omega$ see fig. 10^b		-	120	-	
Fall Time	t _f			-	39	-	
Internal Drain Inductance	L _D	Between lead 6 mm (0.25")	from	-	5.0	-	11
Internal Source Inductance	L _S	package and die contact	center of	-	13	-	- nH
Drain-Source Body Diode Characteristic	s	-				•	
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	7.8	
Pulsed Diode Forward Current ^a	I _{SM}			-	-	31	- A
Body Diode Voltage	V _{SD}	T _J = 25 °C	$I_{S} = 7.8 \text{ A}, V_{GS} = 0 \text{ V}^{b}$	-	-	1.8	V
Body Diode Reverse Recovery Time	t _{rr}	T ₁ =	25 °C, I _F = 7.8 A,	-	650	980	ns
Body Diode Reverse Recovery Charge	Q _{rr}	ď	25 °C, I _F = 7.8 A, /dt = 100 A/μs ^b	-	3.8	5.7	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and		by L _S and	L _D)		

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300 \,\mu s$; duty cycle $\leq 2 \,\%$.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

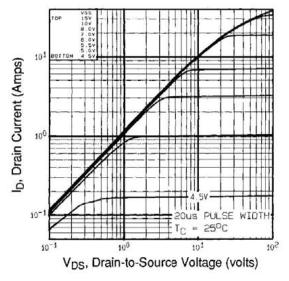


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

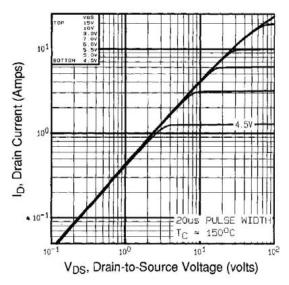


Fig. 2 - Typical Output Characteristics, $T_C = 150$ °C

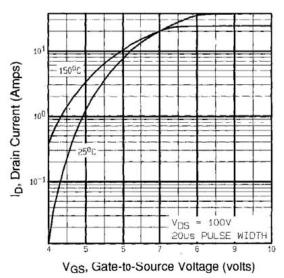


Fig. 3 - Typical Transfer Characteristics

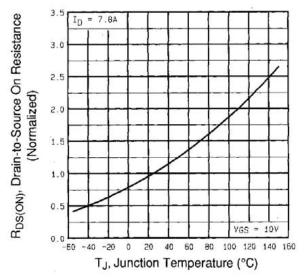


Fig. 4 - Normalized On-Resistance vs. Temperature



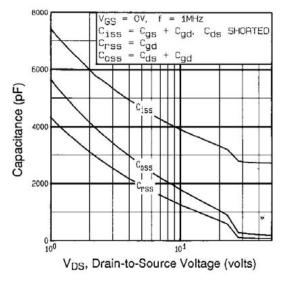


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

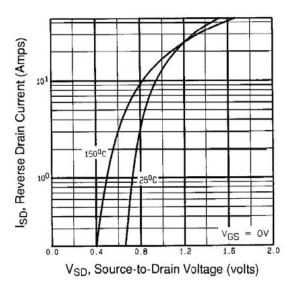


Fig. 7 - Typical Source-Drain Diode Forward Voltage

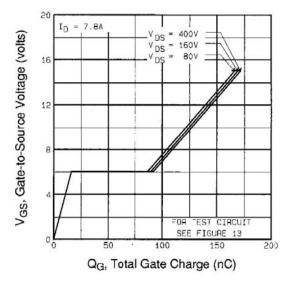


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

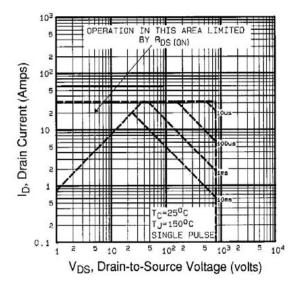


Fig. 8 - Maximum Safe Operating Area





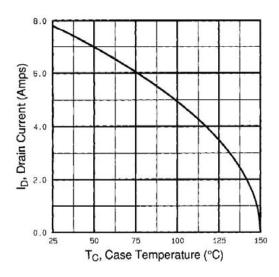


Fig. 9 - Maximum Drain Current vs. Case Temperature

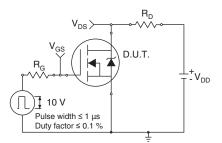


Fig. 10a - Switching Time Test Circuit

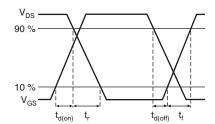


Fig. 10b - Switching Time Waveforms

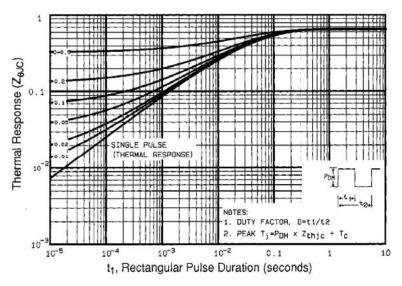


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



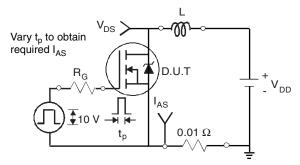


Fig. 12a - Unclamped Inductive Test Circuit

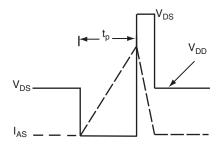


Fig. 12b - Unclamped Inductive Waveforms

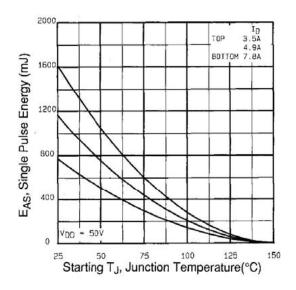


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

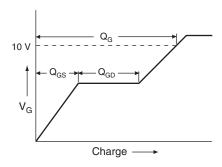


Fig. 13a - Basic Gate Charge Waveform

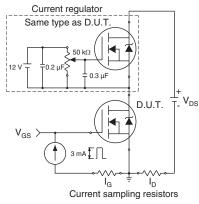
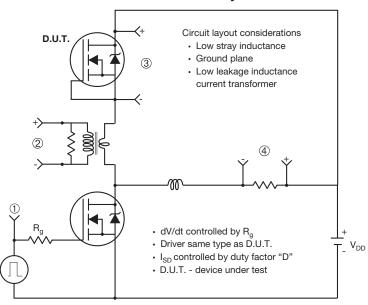


Fig. 13b - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit



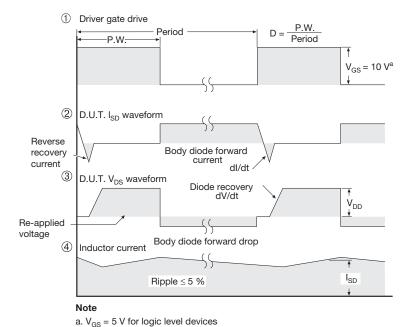


Fig. 14 - For N-Channel

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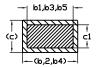


TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

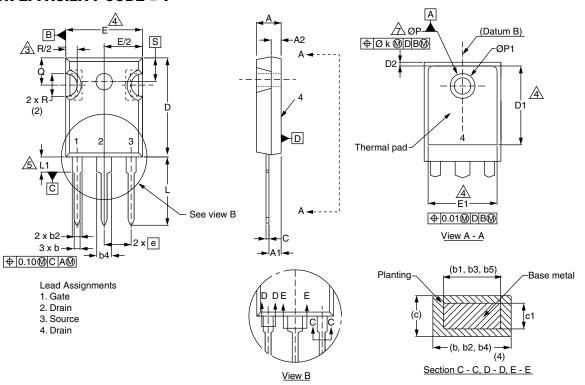
	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

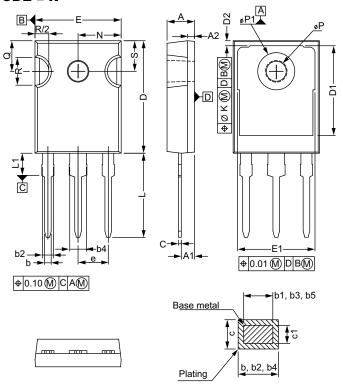
	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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Vishay

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